SKiiP 02NEB066V1



1-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 02NEB066V1

Target Data

Features

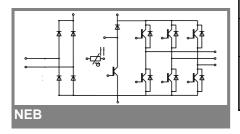
- Trench IGBTs
- · Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL reognised file no. E63532

Typical Applications

- Inverter up to 5 kVA
- Typical motor power 2,2 kW

Remarks

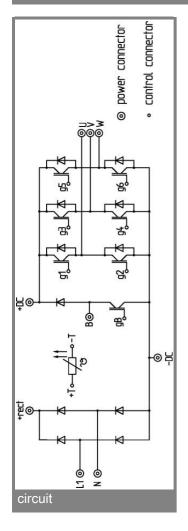
- Case temperature limited to T_C= 125°C max.
- · Product reliability results are valid for T_i= 150°C
- SC data: $t_p \le 6 \ \mu s; \ V_{GE} \le 15 \ V; \ T_j = 150 \ ^{\circ}C; \ V_{CC} = 360 \ V$ V_{CEsat} , V_F = chip level value

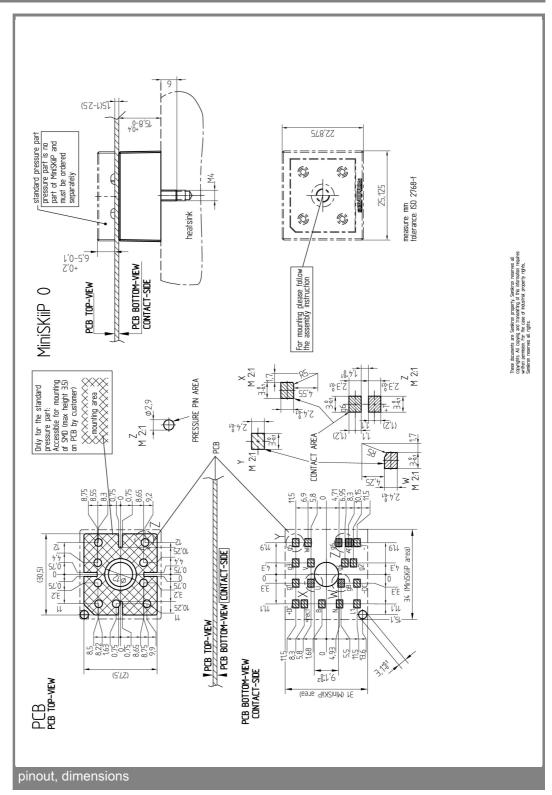


Absolute Maximum Ratings T _S = 25°C, unless otherwise specified							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		600	V				
I _C	$T_s = 25 (70) ^{\circ}C, T_j = 150 ^{\circ}C$	17 (14)	Α				
I _C	$T_s = 25 (70) ^{\circ}C, T_j = 175 ^{\circ}C$	20 (16)	Α				
I _{CRM}	$t_p = 1 \text{ ms}$	20	Α				
V_{GES}		±20	V				
Diode - Inverter, Chopper							
I _F	$T_s = 25 (70) ^{\circ}C, T_i = 150 ^{\circ}C$	20 (15)	Α				
I _F	$T_s = 25 (70) ^{\circ}C, T_j = 175 ^{\circ}C$	22 (18)	Α				
I _{FRM}	$t_p = 1 \text{ ms}$	20	Α				
Diode - Rectifier							
V_{RRM}		800	V				
I _F	T _s = 70 °C	35	Α				
I _{FSM}	$t_p = 10 \text{ ms, sin } 180 ^\circ, T_j = 25 ^\circ\text{C}$	220	Α				
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A²s				
I _{tRMS}	per power terminal (20 A / spring)	20	Α				
T _i	IGBT, Diode	-40+175	°C				
T _{stg}		-40+125	°C				
V _{isol}	AC, 1 min.	2500	V				

Character	istics	T _S = 25°C, unless otherwise specified							
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CE(sat)}	I _{Cnom} = 10 A, T _i = 25 (150) °C		1,45 (1,65)	1,85 (2,05)	V				
$V_{GE(th)}$	V _{GE} = V _{CE} , I _C = 1 mA		5,8		V				
V _{CE(TO)}	T _i = 25 (150) °C		0,9 (0,7)	1,1 (1)	V				
r _{CE}	$T_{j} = 25 (150) ^{\circ}\text{C}$		60 (100)	80 (110)	mΩ				
C _{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,58		nF				
C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,12		nF				
C _{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}$		0,04		nF				
R _{CC'+EE'}	spring contact-chip T _s = 25 (150)°C				mΩ				
$R_{th(j-s)}$	per IGBT		2		K/W				
t _{d(on)}	under following conditions		25		ns				
t _r	$V_{CC} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$		25		ns				
t _{d(off)}	I _{Cnom} = 10 A, T _j = 150 °C		190		ns				
t _f	$R_{Gon} = R_{Goff} = 39 \Omega$		40		ns				
$E_{on} \left(E_{off} \right)$	inductive load		0,5 (0,3)		mJ				
Diode - Inverter, Chopper									
$V_F = V_{EC}$	I _F = 10 A, T _i = 25 (150) °C		1,3 (1,3)	1,6 (1,6)	V				
V _(TO)	T _i = 25 (150) °C		0,9 (0,8)	1 (0,9)	V				
r _T	T _i = 25 (150) °C		40 (50)	60 (70)	mΩ				
$R_{th(j-s)}$	per diode		2,46		K/W				
I _{RRM}	under following conditions		15,8		Α				
Q_{rr}	I _{Fnom} = 10 A, V _R = 300 V		1,5		μC				
E _{rr}	$V_{GE} = 0 \text{ V}, T_j = 150^{\circ}\text{C}$		0,5		mJ				
	di _F /dt = 810 A/μs								
Diode - Rectifier									
V_{F}	I _{Fnom} = 15 A, T _i = 25 °C		1,1		V				
$V_{(TO)}$	T _i = 150 °C		0,8		V				
r _T	$T_{j} = 150 ^{\circ}\text{C}$		20		mΩ				
$R_{th(j-s)}$	per diode		1,5		K/W				
Temperature Sensor									
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω				
Mechanical Data									
w			21,5		g				
M _s	Mounting torque	2		2,5	Nm				

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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